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## Spin-Dependent Electron Transport in MeRAM

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The paper presents theoretical model of a straintronics magnetoelectric random-access memory (MeRAM) storage cell with configurational anisotropy. The MeRAM cell consists of ferromagnetic layers with different orientations of the quasi-uniform magnetization, which is divided into identical magnetic tunnel junction's ferromagnet|insulator|ferromagnet, in the form of a sandwich of planar layers. The modified theory for magnetic tunnel junction is used to calculate the spin-dependent current and tunnel magnetoresistance like functions of orientations magnetizations of layers.

**Keywords:** straintronics, magnetic heterostructure, magnetic tunnel junction, spin-dependent current, tunnel magnetoresistance.